

General Description

This PAP2231H P-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent Rds(On) performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

> Feature

- ●Low Offset (Error) Voltage
- ●Low-Voltage Operation
- High-Speed Circuits
- ●Low Battery Voltage Operation
- ●SOT-363 package design

Application

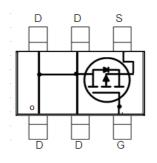
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- ●Load/Power Switching Smart Phones, Pagers
- ●PA Switch
- ●Level Switch

Absolute Maximum Ratings

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V _{DS}	-20	V
Gate-Source Voltage	V _G s	±12	V
Continuous Drain Current, -V _{GS} @ -4.5V ¹	I _D @T _A =25°C	-2.3	А
Continuous Drain Current, -V _{GS} @ -4.5V ¹	I _D @T _A =70°C	-1.8	А
Pulsed Drain Current ²	I _{DM}	-10	А
Total Power Dissipation ³	P _D @T _A =25°C	0.76	W
Total Power Dissipation ³	P _D @T _A =70°C	0.48	W
Storage Temperature Range	T _{STG}	-55 to 150	°C
Operating Junction Temperature Range	TJ	-55 to 150	°C
Thermal Resistance Junction-Ambient ¹	R _θ JA	165	°C/W









Electrical Characteristics (TA=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V , I _D =-250uA	-20			V	
Static Drain-Source On-Resistance ²	D-a/a/ii	V _{GS} =-4.5V , I _D =-1.8A		90	100	mΩ	
	R _{DS(ON)}	V _{GS} =-2.5V , I _D =-1.5A		130	155		
Gate Threshold Voltage	V _{GS(th)}	$V_{GS}=V_{DS}$, I_{D} =-250uA	-0.45		-1.0	V	
Drain-Source Leakage Current	lane	V_{DS} =-16V , V_{GS} =0V , T_{J} =25 $^{\circ}$ C			-1		
	IDSS	VDS=-16V , VGS=0V , TJ=85°C		-30	uA		
Gate-Source Leakage Current	Igss	$V_{GS}=\pm 12V$, $V_{DS}=0V$			±100	nA	
Total Gate Charge	Qg			3.8			
Gate-Source Charge	Q _{gs}	V _{DS} =-10V , V _{GS} =-4.5V , I _D =-1.8A		0.75		nC	
Gate-Drain Charge	Q_{gd}			0.7			
Turn-On Delay Time	T _{d(on)}			3			
Rise Time	Tr	V_{DD} =-10 V , V_{GS} =-4.5 , R_{G} =1 Ω ,		23.5		ns	
Turn-Off Delay Time	T _{d(off)}	I _D =-1.8A		11			
Fall Time	T _f			20			
Input Capacitance	Ciss			312			
Output Capacitance	Coss	V _{DS} =-10V , V _{GS} =0V , f=1MHz		51		pF	
Reverse Transfer Capacitance	Crss			47			

Diode Characteristics

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Continuous Source Current ^{1,4}	Is	V _G =V _D =0V , Force Current			-2.3	Α
Diode Forward Voltage ²	V_{SD}	V _{GS} =0V , I _S =-0.42A , T _J =25°C			-1.2	V

Note:

^{1.}Pulse width limited by maximum junction temperature.

^{2.}The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%

^{3.}Ensure that the channel temperature does not exceed 150°C.

^{4.} The data is theoretically the same as ID and IDM, in real applications, should be limited by total power dissipation.



> Typical Characteristics

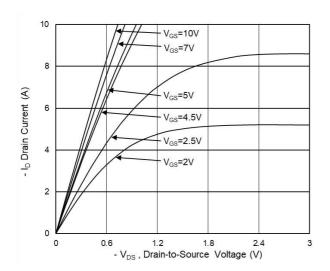


Fig.1 Typical Output Characteristics

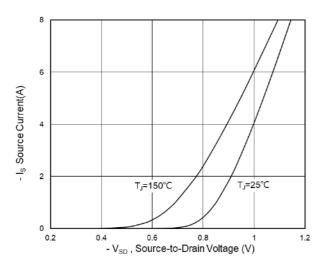


Fig.3 Source Drain Forward Characteristics

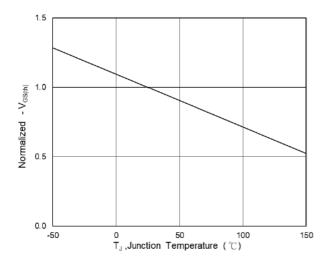


Fig.5 Normalized V_{GS(th)} vs T_J

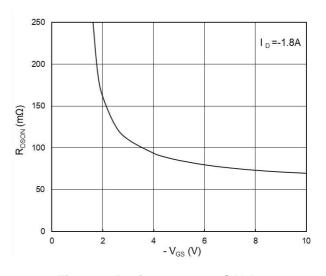


Fig.2 On-Resistance vs G-S Voltage

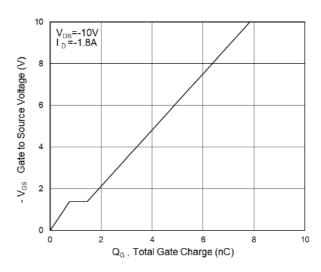


Fig.4 Gate-Charge Characteristics

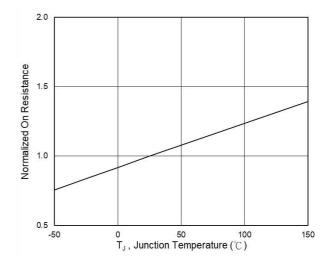
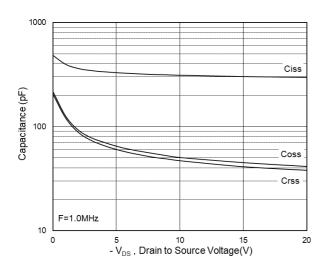


Fig.6 Normalized RDSON vs TJ





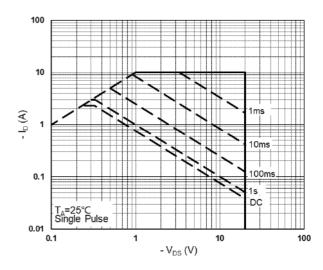


Fig.7 Capacitance

Fig.8 Safe Operating Area

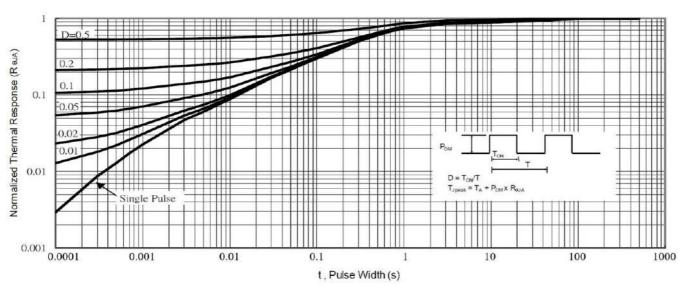
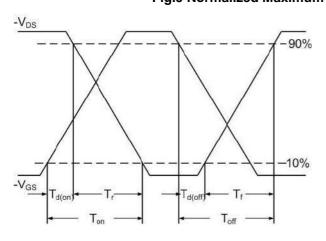


Fig.9 Normalized Maximum Transient Thermal Impedance





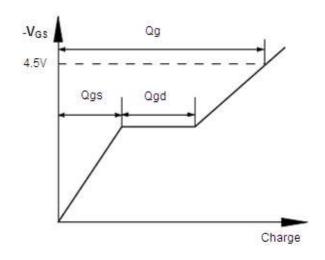
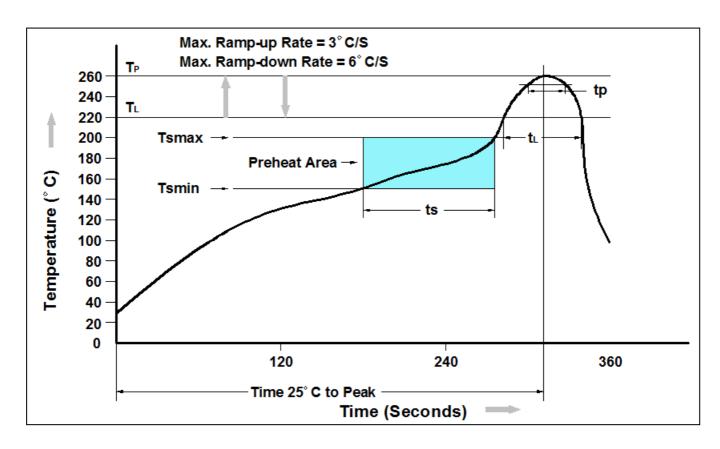


Fig.11 Gate Charge Waveform



Recommand IR Reflow Soldering Thermal Profile



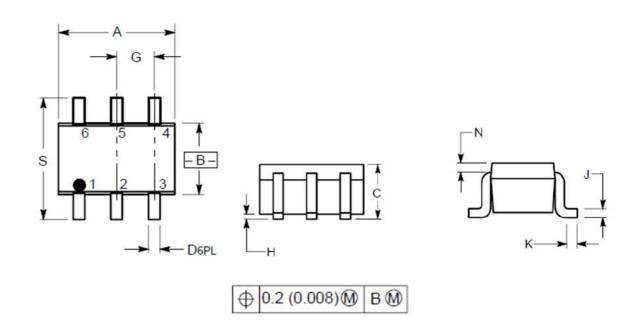
Profile Feature	Pb-Free Assembly Profile		
Temperature Min. (Tsmin)	150°C		
Temperature Max. (Tsmax)	200°C		
Time (ts) from (Tsmin to Tsmax)	60-120 seconds		
Average Ramp-up Rate (tL to tP)	3°C/second max.		
Liquidous Temperature (TL)	217°C		
Time (tL) Maintained Above (TL)	60 – 150 seconds		
Peak Temperature	260°C +0°C /-5°C		
Time (tP) within 5°C of actual Peak Temperature	30 seconds		
Ramp-down Rate (TP to TL)	6°C/second max		
Time 25°C to Peak Temperature	8 minutes max.		

Ordering Information

Part Number	Description	Quantity
PAP2231H	SOT-363 Reel	3000 pcs



Package Information (SOT-363)



DIM	IN	CHES	MILLIMETERS		
	MIN	MAX	MIN	MAX	
Α	0.071	0.087	1.80	2.20	
В	0.045	0.053	1.15	1.35	
С	0.031	0.043	0.80	1.10	
D	0.004	0.012	0.10	0.30	
G	0.026 BSC		0.65 BSC		
Н		0.004		0.10	
J	0.004	0.010	0.10	0.25	
K	0.004	0.012	0.10	0.30	
N	0.008 REF		0.2	20 REF	
S	0.079	0.087	2.00	2.20	



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